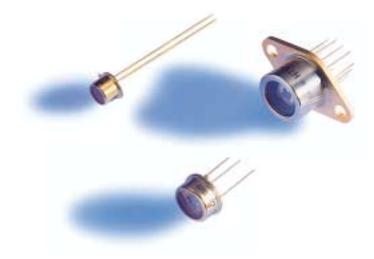


Description

The PerkinElmer family of large-area InGaAs PIN photodiodes provide high responsivity from 800 nm to 1700 nm for applications including optical power meters, fiber optic test equipment, near-IR spectoscopy and instrumentation. All devices are planar passivated and feature low capacitance for extended bandwidth, and high shunt resistance for maximum sensitivity. Typical devices feature <1% non-linearity to optical powers >+13 dBm (20 mW), and uniformity within ±2% across the detector active area. Typical responsivity of 0.2 A/W at 850 nm for our large-area InGaAs devices allows use of a single detector in fiber optic test instrumentation designed to operate at 850, 1300, and 1550 nm.

Devices are available with active areas from 0.5 mm to 3.0 mm in TO-type packages or on thermoelectric coolers for increased sensitivity (see below). Photodiodes can also be mounted on customized ceramic sub-mounts to suit specific application requirements. PerkinElmer Optoelectronics Canada is qualified to ISO-9001 and operates to MIL-Q-9858A and AQAP-1 quality standards. All devices undergo extended life-test and periodic process qualification programs to assure high reliability. In addition, all production devices are sourced from a qualified wafer, screened with a 16 hour, 200°C burn-in at -10V bias (C30619 and C30641) or -5V (C30642 and C30665), and tested to meet responsivity, spectral noise, capacitance, shunt resistance and dark current specifications.

Large-Area InGaAs Photodiodes C30619, C30641, C30642, C30665



Features

- •0.5, 1.0, 2.0, and 3.0 mm diameters
- · High responsivity from 850 nm to 1550 nm
- · High shunt resistance, low dark current
- TE-cooled package options
- · Low capacitance for fast response times

Applications

- Power meters
- Fiber identifiers
- · Laser burn-in racks
- Near infrared instrumentation
- F.T.I.R. spectroscopy







Package Options

TE-Cooled Devices: Large-area detectors are available mounted on a 1-stage or 2-stage thermoelectric (TE) cooler. Cooling increases shunt resistance (see Figure 2) thereby reducing noise for increased sensitivity. Typical detector temperature is -10°C with a 1-stage TE cooler or -35°C using a 2-stage cooler. A TE-cooler option can be specified by adding the extension -TC (1-stage cooler) or -DTC (2-stage cooler) to the standard part number (see ordering guide). More information is available from the "TC-Series Cooled Photodiodes" datasheet from PerkinElmer Optoelectronics Canada.

Detector and Pre-Amplifier: Large-area InGaAs detectors are also available integrated with a preamplifier and TE-cooler. The HTE-series features large-area InGaAs detectors with a high gain hybrid transimpedence amplifier mounted on a 2-stage TE cooler. TE-cooling maximizes sensitivity and stabilizes op-amp offset and output characteristics. This provides an easy-to-use high sensitivity detector platform optimized for good temperature stability over a wide operating temperature range. More information is available from the HTE-series datasheet. The standard HTE-2642 incorporates a C30642E chip.

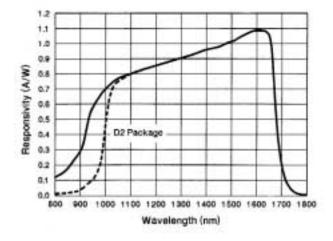
Specifications (at V _R = V _{OP} (typical), 22°C)								
Parameter	C30619				C30641		Units	
	Min	Тур	Max	Min	Тур	Max		
Active Diameter		0.5			1.0		mm	
Responsivity At 850 nm	0.10	0.20		0.10	0.20		A/W	
At 1300 nm	0.80	0.90		0.80	0.90		A/W	
At 1550 nm	0.85	0.95		0.85	0.95		A/W	
Shunt Resistance (V _R = 10 mV) ¹	10	250		5	50		ΜΩ	
Dark Current		1	20		5	50	nA	
Spectral Noise Current (10 kHz, 1.0	Hz)	0.02	0.10		0.04	0.15	pA∕√Hz	
Capacitance At V _R = 0V		20	25		100	125	pF	
At V _R = V _{OP}		8	10		40	50	pF	
Bandwidth (-3 dB, $R_L = 50\Omega$)		350			75		MHz	
Linearity ²		>+13			>+13		dBm	
Available package types		D2. D14			D2. D14		-	

Operating Ratings								
Parameter	C30619			C30641			Units	
	Min	Тур	Max	Min	Тур	Max		
Operating Voltage	0	5	10	0	2	5	V	
Breakdown Voltage	20	80		20	80		V	
Maximum Forward Current			10			10	mA	
Maximum Photocurrent			100			100	mA	
Power Dissipation			100			100	mW	
Storage Temperature	-60		125	-80		125	°C	
Operating Temperature	-40		85	-40		85	°C	

Note 1. Selected higher shunt resistance devices are available to special order.

Note 2. Maximum optical power level for < ± 0.04 dB ($\pm 1\%$) responsivity variation under 1300 nm CW illumination, at $V_{R} = V_{OP}$ (typ).





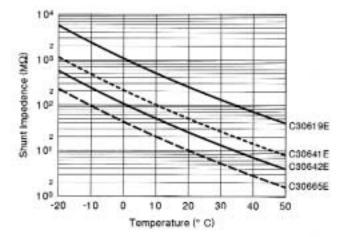


Figure 1. Typical Responsivity vs. Wavelength.

Figure 2. Typical Shunt Resistance as a Function of Temperature.

Specifications (at V _R = V _{OP} (typical), 22°C)								
Parameter	C30642				C30665		Units	
	Min	Тур	Max	Min	Тур	Max		
Active Diameter		2.0			3.0		mm	
Responsivity At 850 nm	0.10	0.20		0.10	0.20		A/W	
At 1300 nm	0.80	0.90		0.80	0.90		A/W	
At 1550 nm	0.85	0.95		0.85	0.95		A/W	
Shunt Resistance (V _R = 10 mV) ¹	2	25		1	10		ΜΩ	
Dark Current		10 ³			25 ³		nA	
Spectral Noise Current (10 kHz, 1.0	Hz)	0.03	0.15		0.04	0.20	pA∕√Hz	
Capacitance At V _R = 0V		300	500		1000	1250	pF	
At V _R = 2.0V (typical)		150			400		pF	
Bandwidth (-3 dB, $R_L = 50\Omega$)		20			3.0		MHz	
Linearity ²		+11			+11		dBm	
Available package types		D15			D15		-	

Operating Ratings								
Parameter	C30642			C30665			Units	
	Min	Тур	Max	Min	Тур	Max		
Operating Voltage		0	5		0	5	V	
Breakdown Voltage	15	50		10	50		V	
Maximum Forward Current			10			10	mA	
Maximum Photocurrent			100			100	mA	
Power Dissipation			250			250	mW	
Storage Temperature	-60		125	-80		125	°C	
Operating Temperature	-40		85	-40		85	°C	

Note 1. Selected higher shunt resistance devices are available to special order.

Note 2. Maximum optical power level for < ± 0.04 dB ($\pm 1\%$) responsivity variation under 1300 nm CW illumination, at $V_R = V_{OP}$ (typ).

Note 3. At $V_R = 2.0V$



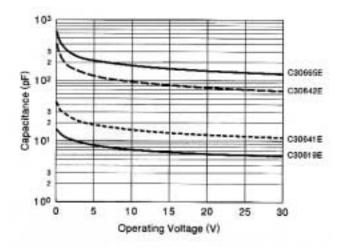


Figure 3. Typical Capacitance vs. Operating Voltage.

Wavelength	Temperature Coefficient ¹	
(nm)	(%/°C)	
850	-0.121	
1060	0.039	
1300	0.012	
1550	0.009	
1650	0.085	(20°C to 85°C)
	1.287	(-40°C to 20°C)

Note1: Measured from -40°C to +85°C except 1650nm, as indicated.

Figure 5. Typical Responsivity Temperature Coefficients.

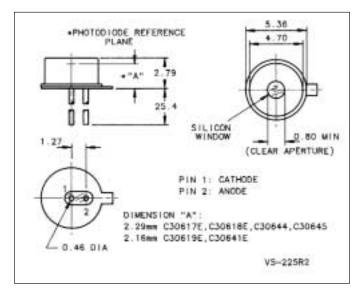


Figure 7. Package D2: TO-18 Low Profile with Silicon Window. To special order.

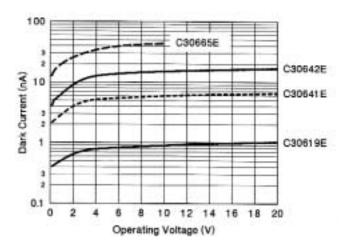


Figure 4. Typical Dark Current vs. Operating Voltage.

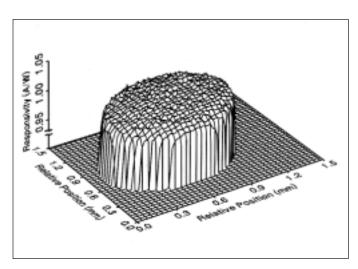


Figure 6. Typical Responsivity Scan of a 1mm Photodiode.

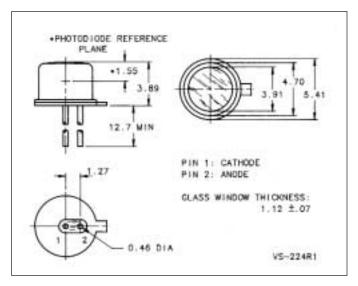


Figure 8. Package D-14: TO-18 with Glass Window.



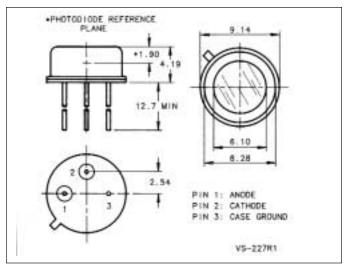
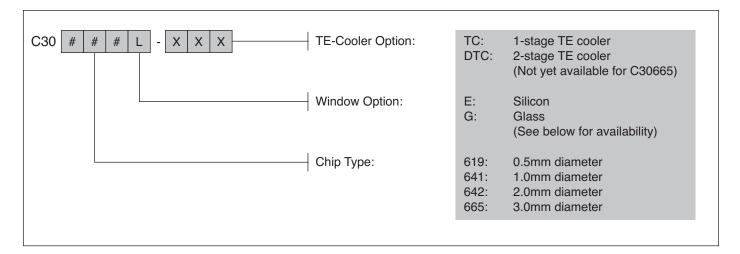


Figure 9. Package D15: TO-5 with Glass Window.

Ordering Guide



Device Package Availability

Window	Window	low Package Type						
Option	Type	C30619	C30641	C30642	C30665			
E	Silicon	D2 ¹	D2 ¹	-	-			
G	Glass	D14	D14	D15	D15			

Note 1: Special Order



 $For more information \ e-mail \ us \ at \ opto@perkinelmer.com \ or \ visit \ our \ web \ site \ at \ www.perkinelmer.com/opto$

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